## NSN 5961-00-419-5367



Transistor - Page 1 of 2 View Online at https://aerobasegroup.com/nsn/5961-00-419-5367 **Inclosure Material:** Metal **Overall Length:** 1.572 inches **Overall Height:** 0.562 inches **Overall Width:** 1.050 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: To-3 **Electrode Internally-electrically Connected To Case:** Collector **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 100.0 collector to base voltage/static/emitter open and 100.0 collector to emitter voltage, dc with specified circuit between base and emitter and 55.0 collector to emitter voltage/static/base open and 10.0 emitter to base voltage, static, collector open **Current Rating Per Characteristic:** 6.00 amperes source cutoff current and 3.00 amperes source cutoff current **Power Rating Per Characteristic:** 75.0 watts small-signal input power, common-collector **Transfer Ratio:** 16.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Special Features:** Junction pattern arrangement: npn **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life:

Demilitarization:

**Unit Of Measure:** 

No

N/a

## **NSN 5961-00-419-5367** Transistor - Page 2 of 2



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